

Amendments to the Specification:

Please amend the paragraph beginning at page 6, line 16, of the specification as follows:

As shown in Figs. 6 and 7, sidewall insulating film 6 is formed to cover a side of dual-gate electrode 4 covered with gate-etching mask 5. It is noted that, before sidewall insulating film 6 is formed, a source/drain region 14 is formed in the active region which is exposed to sandwich dual-gate electrode 4 in plan view.

Please amend the paragraph beginning at page 7, line 5, of the specification as follows:

Figs. 10 and 11 show a graph illustrating how a junction leakage current I_H changes with respect to an applied voltage V_H . Some conventional configurations having contacts overlapping a silicide region show a junction leakage current which varies as shown in Fig. 11. In contrast, a configuration to which the present invention is applied to have contacts without overlapping a silicide region shows a junction leakage current which varies to a smaller degree as shown in Fig. 10, and thus the junction leakage current can be controlled.